Product data sheet

1. Product profile

1.1 General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a medium power and flat lead SOT89 (SC-62) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4032NX.

1.2 Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- Optimized switching time
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High energy efficiency due to less heat generation
- AEC-Q101 qualified
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

1.3 Applications

- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-30	V
I _C	collector current		-	-	-4.2	Α
I _{CM}	peak collector current	$\begin{array}{l} \text{single pulse;} \\ t_p \leq 1 \text{ ms} \end{array}$	-	-	-10	Α
R _{CEsat}	collector-emitter saturation resistance	$I_{C} = -4 \text{ A};$ $I_{B} = -400 \text{ mA}$	<u>[1]</u> -	58	86	mΩ

[1] Pulse test: $t_p \leq 300~\mu s;~\delta \leq 0.02.$



2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	emitter		_
2	collector		2
3	base	3 2 1	3 —
			00622231

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS4032PX	SC-62	plastic surface-mounted package; 3 leads	SOT89

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PBSS4032PX	*6J

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

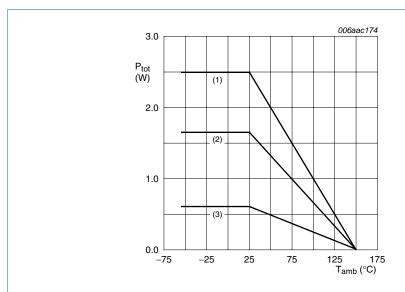
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-30	V
V_{CEO}	collector-emitter voltage	open base	-	-30	V
V_{EBO}	emitter-base voltage	open collector	-	-5	V
I _C	collector current		-	-4.2	Α
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-10	Α
I _B	base current		-	-1	Α

Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
P_{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> -	600	mW
			[2] -	1650	mW
			[3] _	2500	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, standard footprint

Fig 1. Power derating curves

Thermal characteristics

Table 6. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$ thermal resistance from junction to ambient	thermal resistance from	in free air	<u>[1]</u> -	-	210	K/W
	junction to ambient		[2] _	-	75	K/W
			<u>[3]</u> _	-	50	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	20	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

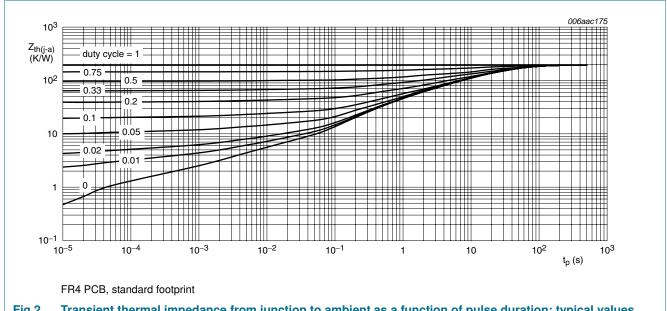


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

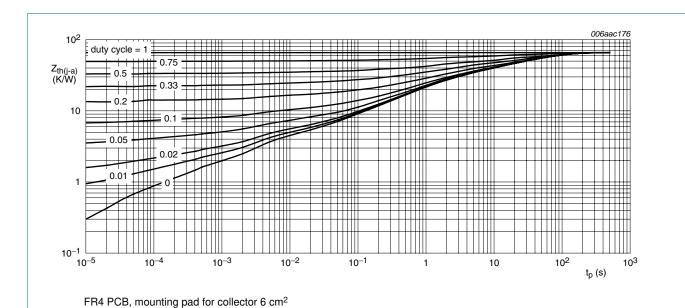
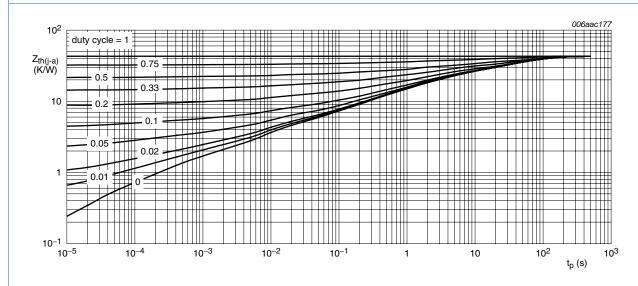


Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Ceramic PCB, Al₂O₃, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

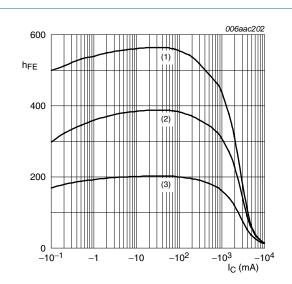
7. Characteristics

Table 7. Characteristics

 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}$		-	-	-100	nA
	current	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 ^{\circ}\text{C}$		-	-	-50	μА
I _{CES}	collector-emitter cut-off current	$V_{CE} = -24 \text{ V}; V_{BE} = 0 \text{ V}$		-	-	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$		-	-	-100	nA
h _{FE} DC current gain		$V_{CE} = -2 V$	[1]				
		$I_{C} = -500 \text{ mA}$		200	350	-	
		$I_C = -1 A$		200	320	-	
		$I_C = -2 A$		150	240	-	
		$I_C = -4 A$		60	100	-	
V _{CEsat} collector-emitter			[1]				
saturation voltage	saturation voltage	$I_C = -1 A$; $I_B = -50 \text{ mA}$		-	-110	-165	mV
		$I_C = -1 A$; $I_B = -10 \text{ mA}$		-	-160	-240	mV
		$I_C = -2 \text{ A}; I_B = -40 \text{ mA}$		-	-200	-300	mV
		$I_C = -4 \text{ A}; I_B = -400 \text{ mA}$		-	-230	-345	mV
	$I_C = -4 \text{ A}; I_B = -200 \text{ mA}$		-	-270	-400	mV	
R _{CEsat}	collector-emitter saturation resistance	$I_C = -4 A$; $I_B = -400 \text{ mA}$	[1]	-	58	86	mΩ
V _{BEsat}	base-emitter	$I_C = -1 A$; $I_B = -50 \text{ mA}$	[1]	-	-0.78	-0.9	٧
	saturation voltage	$I_C = -4 \text{ A}; I_B = -400 \text{ mA}$	[1]	-	-1.02	-1.1	٧
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = -2 \text{ V}; I_C = -2 \text{ A}$	[1]	-	-0.81	-0.9	V
t _d	delay time	$V_{CC} = -12.5 \text{ V};$		-	30	-	ns
t _r	rise time	$I_{C} = -1 \text{ A}; I_{Bon} = -0.05 \text{ A};$		-	60	-	ns
t _{on}	turn-on time	$I_{Boff} = 0.05 A$		-	90	-	ns
t _s	storage time			-	140	-	ns
t _f	fall time			-	80	-	ns
t _{off}	turn-off time			-	220	-	ns
f _T	transition frequency	$V_{CE} = -10 \text{ V};$ $I_{C} = -100 \text{ mA};$ $f = 100 \text{ MHz}$		-	115	-	MHz
C _c	collector capacitance	$V_{CB} = -10 \text{ V};$ $I_E = i_e = 0 \text{ A}; f = 1 \text{ MHz}$		-	85	-	pF

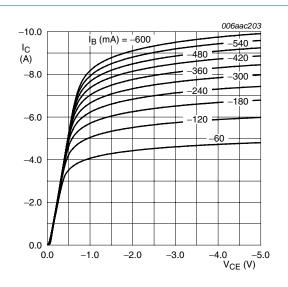
^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$



$$V_{CE} = 2 V$$

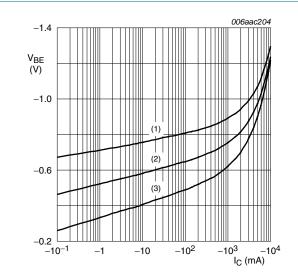
- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

Fig 5. DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

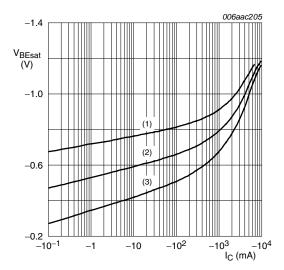
Fig 6. Collector current as a function of collector-emitter voltage; typical values





- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

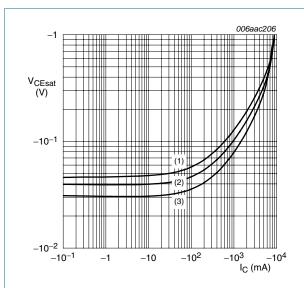
Fig 7. Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 8. Base-emitter saturation voltage as a function of collector current; typical values

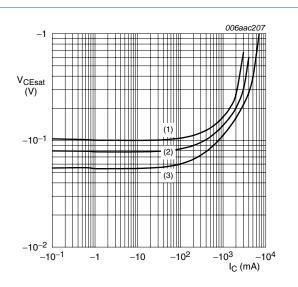


$$I_{C}/I_{B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values



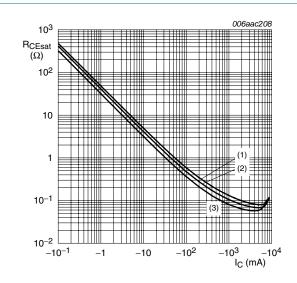
$$T_{amb} = 25 \, ^{\circ}C$$

(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig 10. Collector-emitter saturation voltage as a function of collector current; typical values



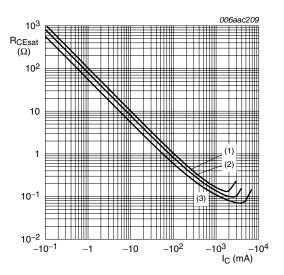
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 11. Collector-emitter saturation resistance as a function of collector current; typical values



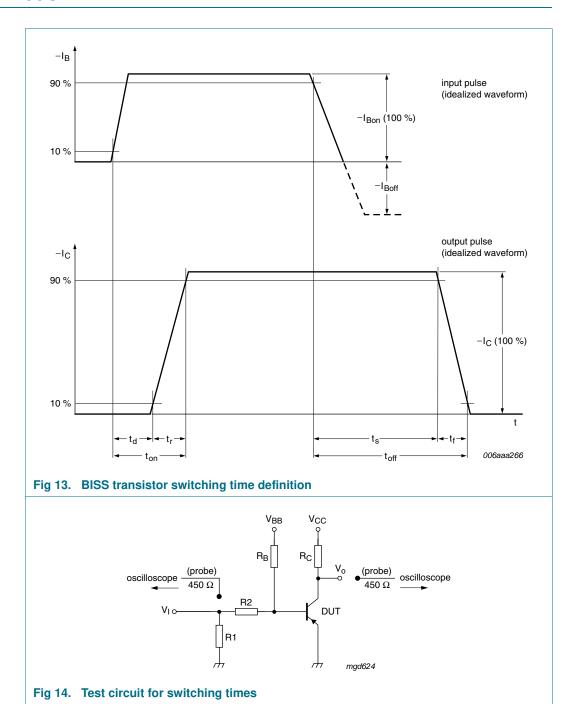
(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values

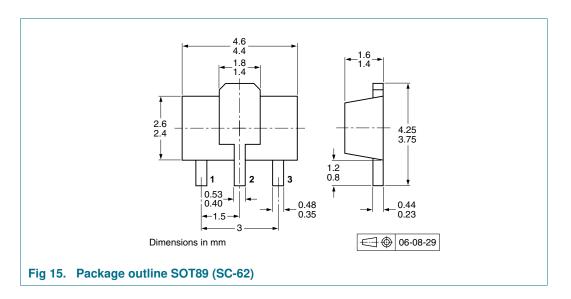
8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

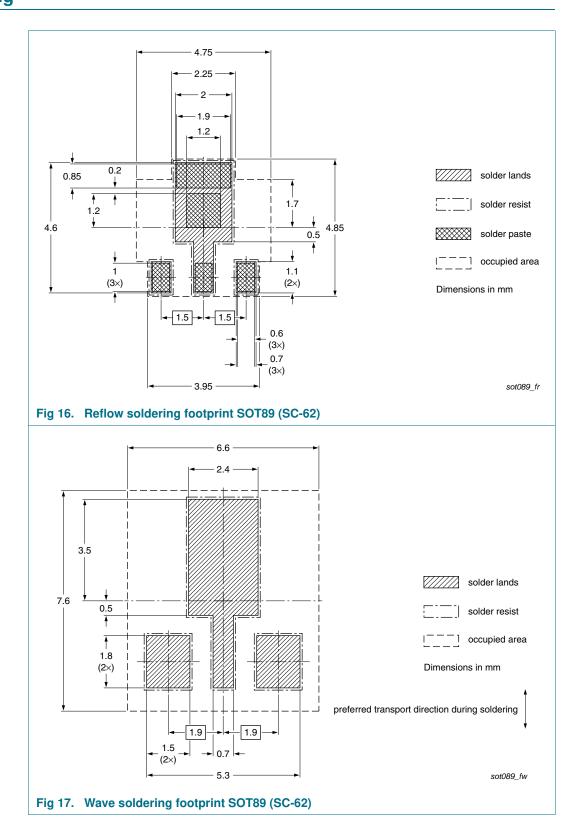
Type number	Package	Description		Packing quantity	
				3000	10000
PBSS4032PX	SOT89	8 mm pitch, 12 mm tape and reel; T1	[2]	-115	-135
		8 mm pitch, 12 mm tape and reel; T3	[3]	-120	-

^[1] For further information and the availability of packing methods, see Section 14.

^[2] T1: normal taping

^[3] T3: 90° rotated taping

11. Soldering



PBSS4032PX

Nexperia

30 V, 4.2 A PNP low V_{CEsat} (BISS) transistor

12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4032PX_1	20100401	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PBSS4032PX

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Nexperia PBSS4032PX

30 V, 4.2 A PNP low V_{CEsat} (BISS) transistor

14. Contact information

For more information, please visit: http://www.nexperia.com

For sales office addresses, please send an email to: salesaddresses@nexperia.com

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